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FQA6N90C_F109 N-Channel QFET[®] MOSFET 900 V, 6 A, 2.3 Ω

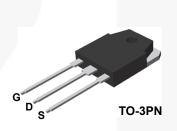
Features

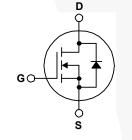
- 6 A, 900 V, $R_{DS(on)}$ = 2.3 Ω (Max.) @ V_{GS} = 10 V, I_D = 3 A
- Low Gate Charge (Typ. 30 nC)
- Low Crss (Typ. 11 pF)
- 100% Avalanche Tested
- RoHS Compliant

FQA6N90C_F109 — N-Channel QFET[®] MOSFET

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQA6N90C_F109	Unit	
V _{DSS}	Drain-Source Voltage		900	V	
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		6.0	А	
	- Continuous (T _C = 100°C)		3.87	А	
I _{DM}	Drain Current - Pulsed	(Note 1)	24.0	А	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy		650	mJ	
I _{AR}	Avalanche Current	(Note 1)	6.0	А	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	19.8	mJ	
dv/dt	Peak Diode Recovery dv/dt		4.0	V/ns	
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		198	W	
	- Derate above 25°C		1.59	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FQA6N90C_F109	Unit	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.63	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient, Max	40	°C/W	

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Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA6N90C_F109	FQA6N90C	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	900			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu A$, Referenced to $25^{\circ}C$		1.07		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 900 V, V _{GS} = 0 V			10	μA
		V _{DS} = 720 V, T _C = 125°C	-		100	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	1		100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V			-100	nA
On Charact	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 3.0 A		1.93	2.3	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 3.0 A	-	5.5		S
Dynamic Cl	haracteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 V, V_{GS} = 0 V,$		1360	1770	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		110	145	pF
C _{rss}	Reverse Transfer Capacitance			11	15	pF
Switching C	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 450 V, I _D = 6.0A,		35	80	ns
t _r	Turn-On Rise Time	- R _G = 25 Ω -		90	190	ns
t _{d(off)}	Turn-Off Delay Time			55	120	ns
t _f	Turn-Off Fall Time	– (Note 4)		60	130	ns
Qg	Total Gate Charge	V _{DS} = 720 V, I _D = 6.0A,		30	40	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		9.0		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		12		nC
Drain-Source	Diode Characteristics and Maximum Ratings	5				
I _S	Maximum Continuous Drain-Source Diode Forward Current				6.0	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				24	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 6.0 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 6.0 A,		630		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		6.9		μC

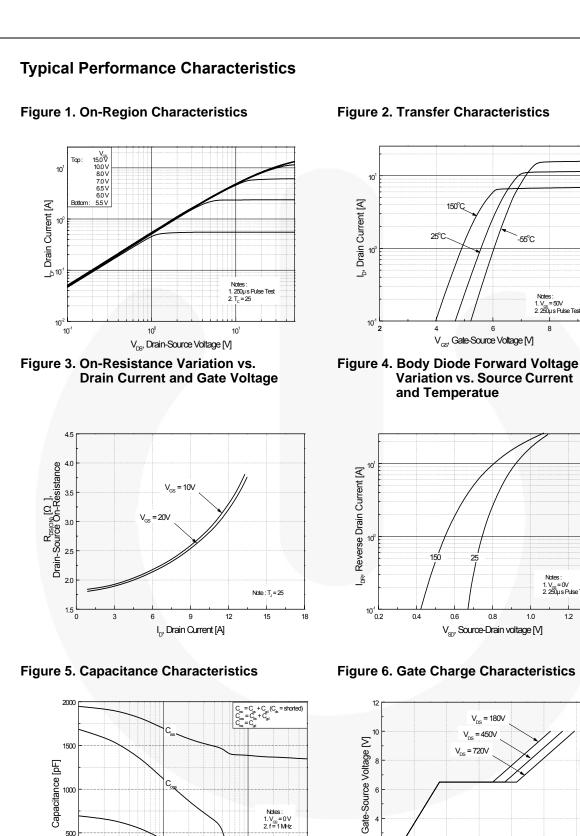
NOTES:

1. Repetitive rating: pulse-width limited by maximum junction temperature.

2. L = 34 mH, I_{AS} = 6 A, V_{DD} = 50 V, R_G = 25 $\Omega,$ starting T_J = 25°C.

 $3.I_{SD} \leq 6$ A, di/dt ≤ 200 A/µs, $V_{DD} \leq BV_{DSS}$, starting T_J = $25^{\circ}C.$

4. Essentially independent of operating temperature typical characteristics.



Notes : 1. V_{DS} = 50V 2. 250µ s Pulse Test

Notes : 1. V_{GS} = 0V 2. 250µs Pulse Test

1.2

Note : $I_D = 6A$

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V_{DS}, Drain-Source Voltage [V]

10¹

0 L

3

 $<_{\rm GS'}$

0 0

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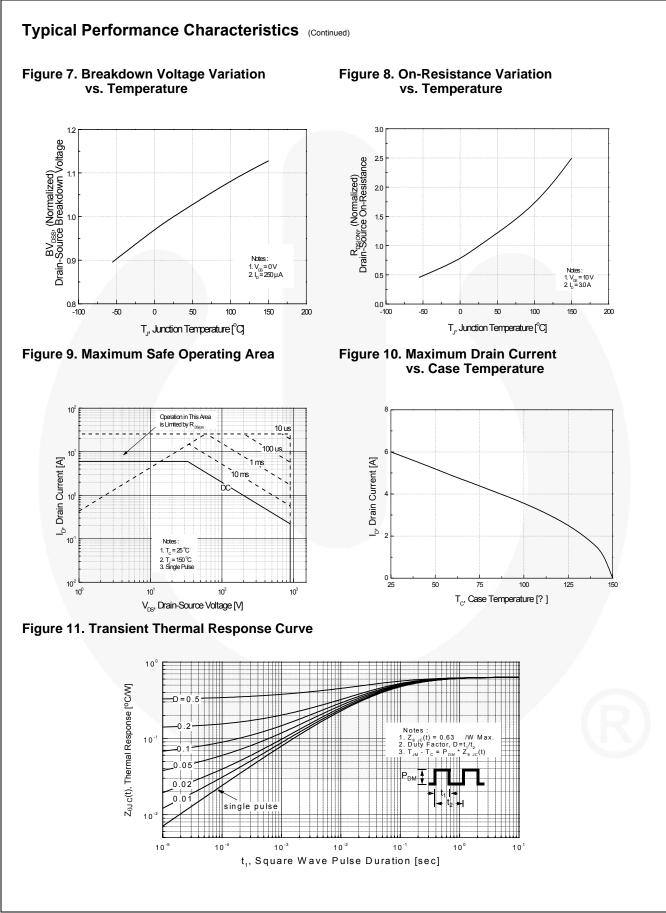
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Q_c, Total Gate Charge [nC]

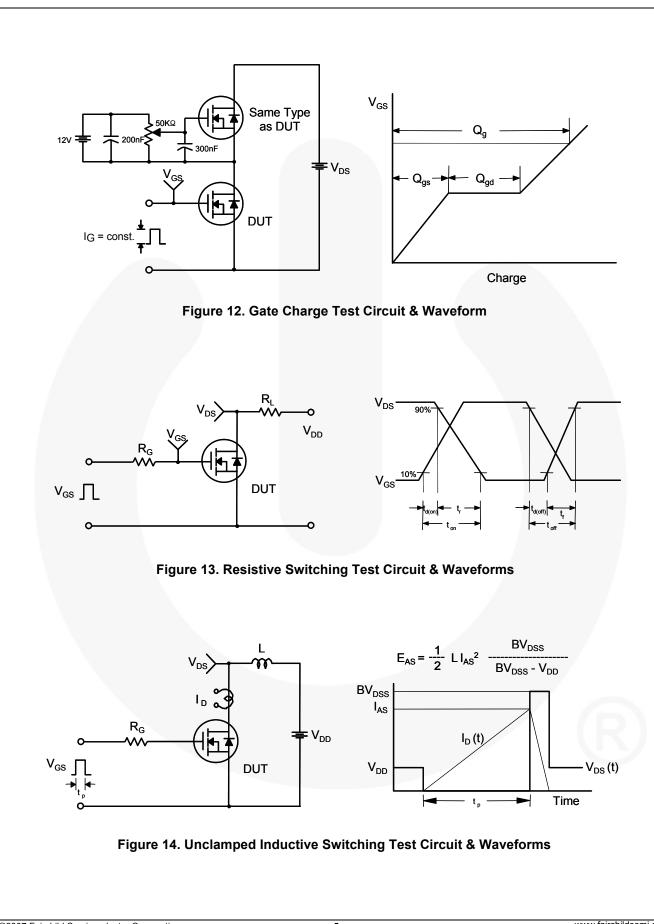
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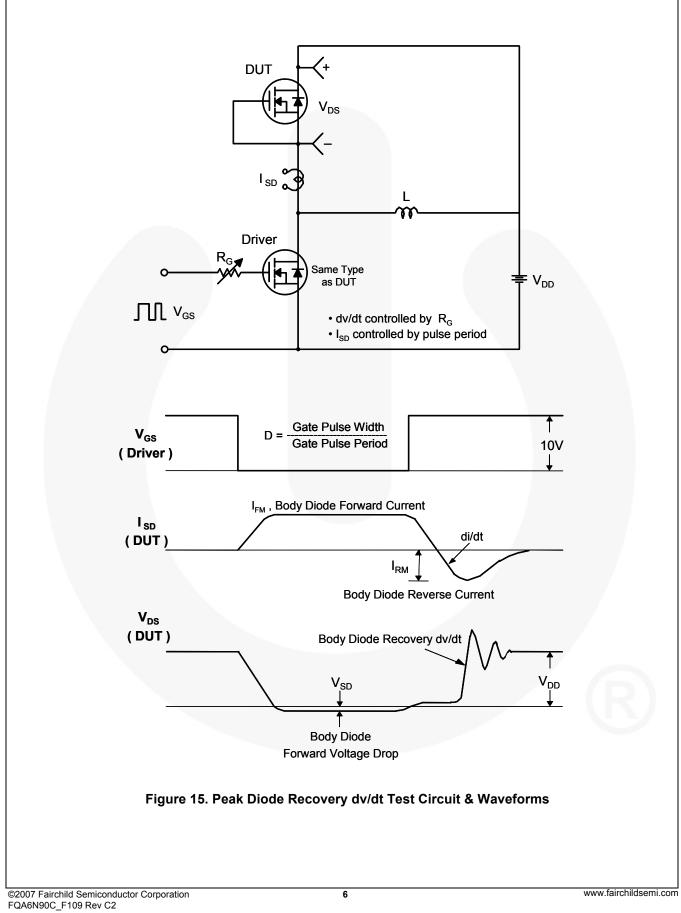


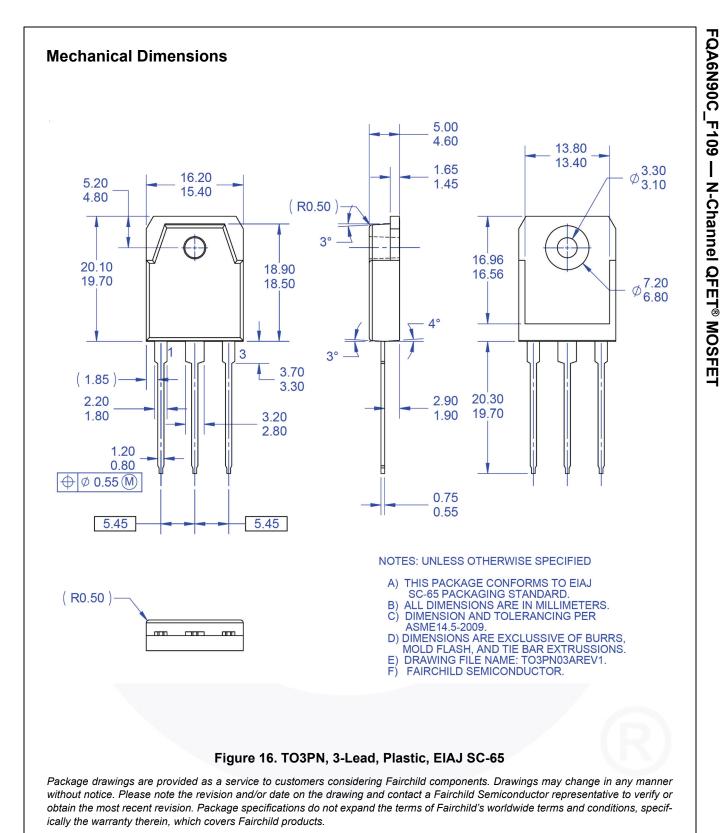
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http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT3PN-003



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